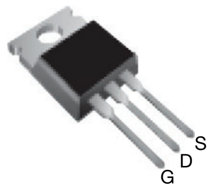
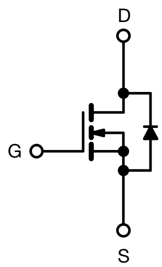
Power MOSFET

TO-220AB





N-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Ultra low on-resistance
- Very low thermal resistance
- 175 °C operating temperature
- Fast switching
- Ease of paralleling
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Available
RoHS*
Available

Note
* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

PRODUCT SUMMARY		
V_{DS} (V)	60	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.018
Q_g (Max.) (nC)	110	
Q_{gs} (nC)	29	
Q_{gd} (nC)	36	
Configuration	Single	

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

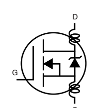
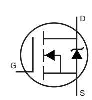
ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRFZ48PbF

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	60	V
Gate-source voltage			V_{GS}	± 20	
Continuous drain current	V_{GS} at 10 V	T_C = 25 °C	I_D	50	A
		T_C = 100 °C		50	
Pulsed drain current [a]			I_{DM}	290	
Linear derating factor				1.3	W/°C
Single pulse avalanche energy [b]			E_{AS}	100	mJ
Repetitive avalanche current [a]			I_{AR}	50	A
Repetitive avalanche energy [a]			E_{AR}	19	mJ
Maximum power dissipation	T_C = 25 °C		P_D	190	W
Peak diode recovery dV/dt [c]			dV/dt	4.5	V/ns
Operating junction and storage temperature range			T_J, T_{stg}	- 55 to + 175	°C
Soldering recommendations (peak temperature) [d]	For 10 s			300	
Mounting torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. V_{DD} = 25 V, starting T_J = 25 °C, L = 22 μH, R_g = 25 Ω I_{AS} = 72 A (see fig. 12)
c. I_{SD} ≤ 72 A, dI/dt ≤ 200 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 175 °C
d. 1.6 mm from case
e. Current limited by the package, (die current = 72 A)

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	0.80	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA		60	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA		-	0.060	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 μA		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 20		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V		-	-	25	μA
		V_{DS} = 48 V, V_{GS} = 0 V, T_J = 150 °C		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 43 A[b]	-	-	0.018	Ω
Forward transconductance	g_{fs}	V_{DS} = 25 V, I_D = 43 A[b]		27	-	-	S
Dynamic							
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	2400	-	pF
Output capacitance	C_{oss}			-	1300	-	
Reverse transfer capacitance	C_{rss}			-	190	-	
Total gate charge	Q_g	V_{GS} = 10 V	I_D = 72 A, V_{DS} = 48 V, see fig. 6 and 13[b]	-	-	110	nC
Gate-source charge	Q_{gs}			-	-	29	
Gate-drain charge	Q_{gd}			-	-	36	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 30 V, I_D = 72 A, R_g = 9.1 Ω, R_D = 0.34 Ω, see fig. 10[b]		-	8.1	-	ns
Rise time	t_r			-	250	-	
Turn-off delay time	$t_{d(off)}$			-	210	-	
Fall time	t_f			-	250	-	
Internal drain inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal source inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	50[c]	A
Pulsed diode forward current [a]	I_{SM}			-	-	290	
Body diode voltage	V_{SD}	T_J = 25 °C, I_S = 72 A, V_{GS} = 0 V[b]		-	-	2.0	V
Body diode reverse recovery time	t_{rr}	T_J = 25 °C, I_F = 72 A, dI/dt = 100 A/μs[b]		-	120	180	ns
Body diode reverse recovery charge	Q_{rr}			-	0.50	0.80	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %

c. Current limited by the package, (die current = 72 A)

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

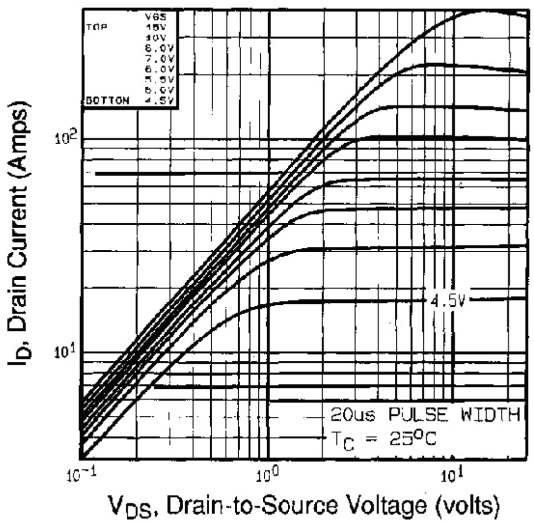


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

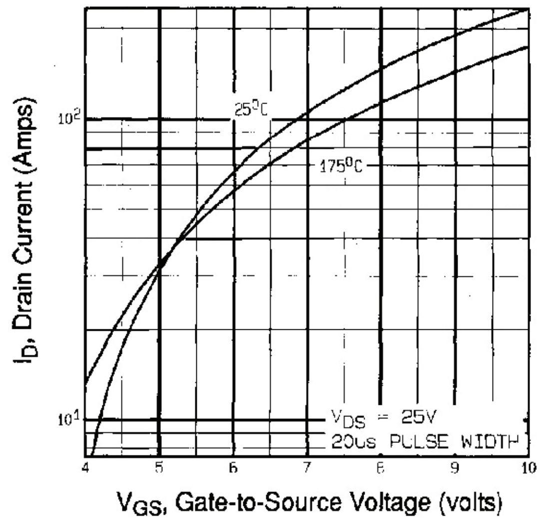


Fig. 3 - Typical Transfer Characteristics

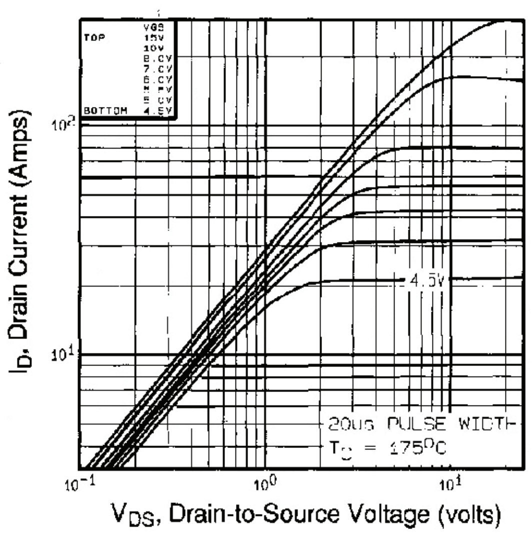


Fig. 2 - Typical Output Characteristics, T_C = 175 °C

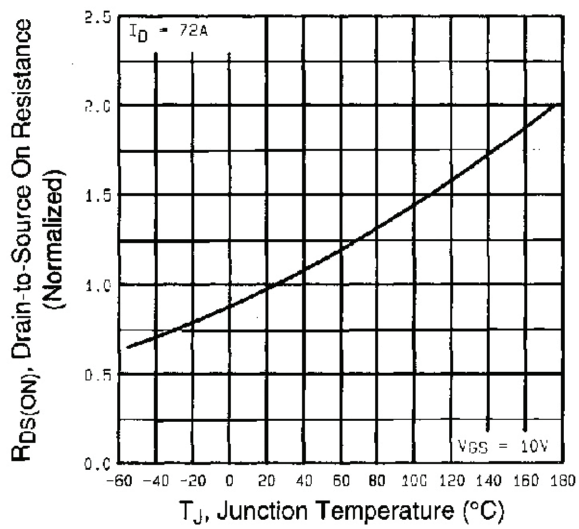


Fig. 4 - Normalized On-Resistance vs. Temperature

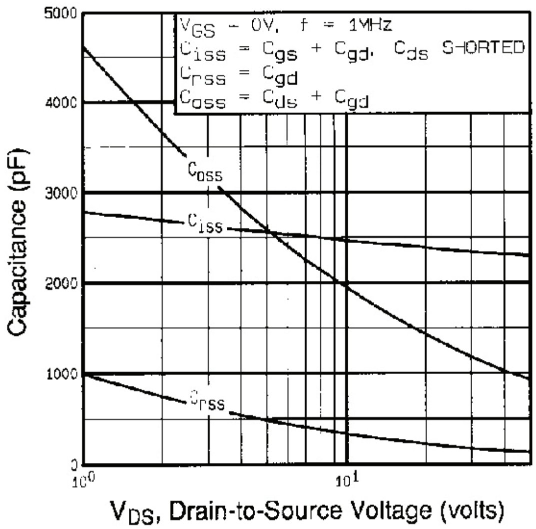


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

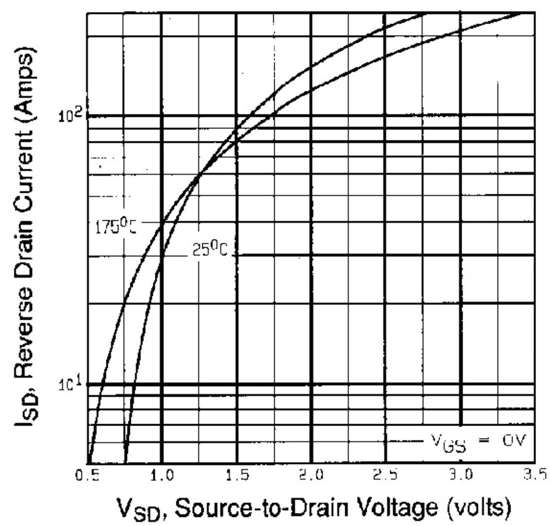


Fig. 7 - Typical Source-Drain Diode Forward Voltage

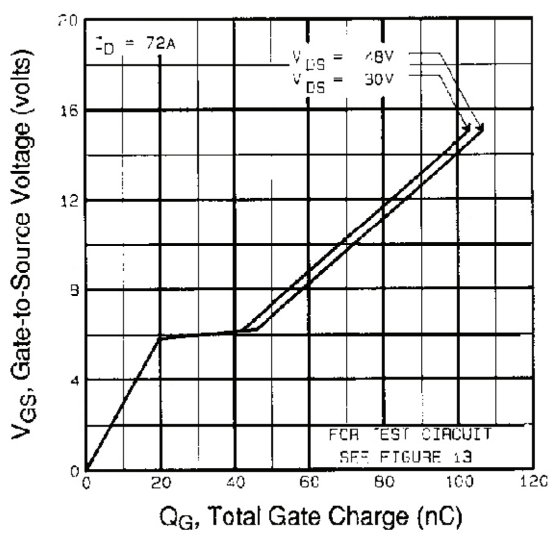


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

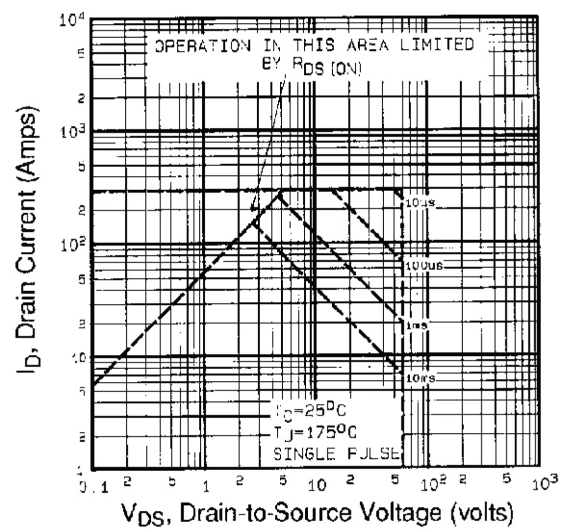


Fig. 8 - Maximum Safe Operating Area

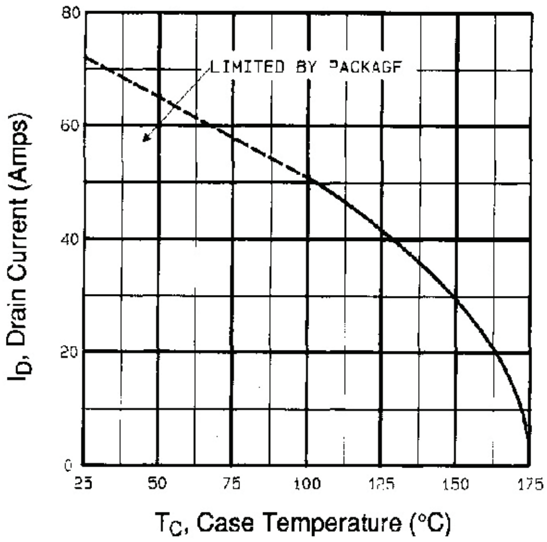


Fig. 9 - Maximum Drain Current vs. Case Temperature

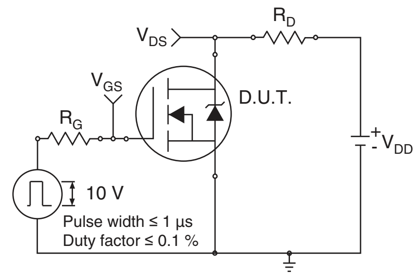


Fig. 10a - Switching Time Test Circuit

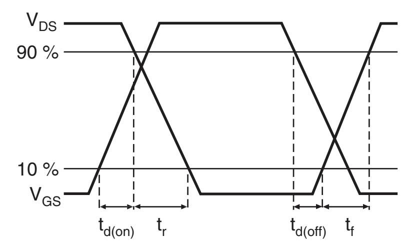


Fig. 10b - Switching Time Waveforms

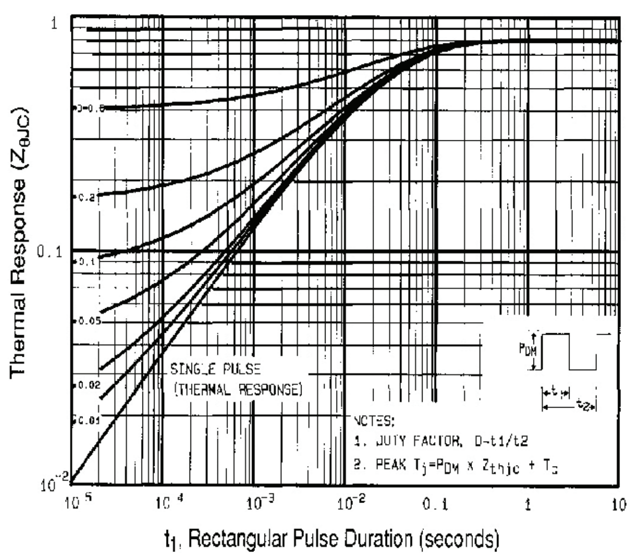


Fig. 10 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

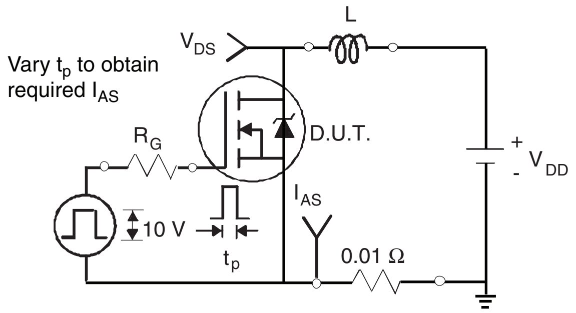


Fig. 12a - Unclamped Inductive Test Circuit

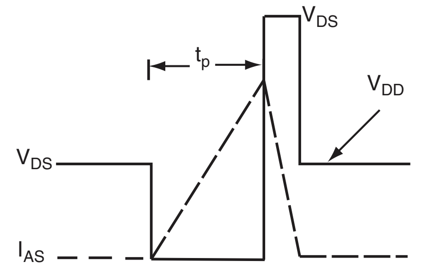


Fig. 12b - Unclamped Inductive Waveforms

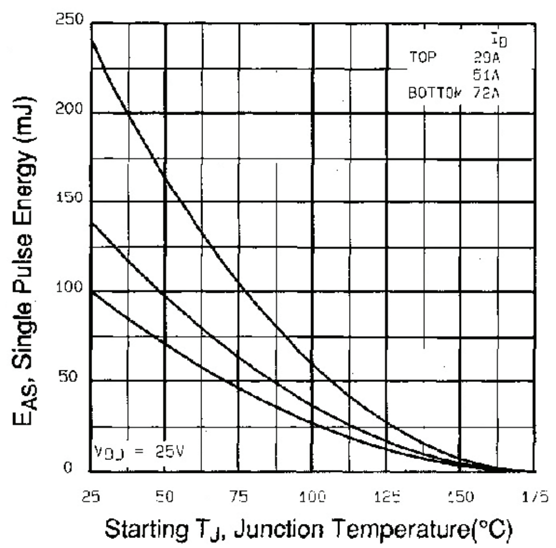


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

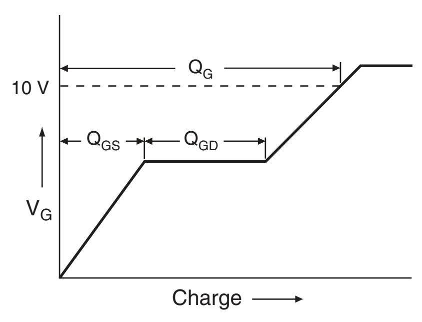


Fig. 13a - Basic Gate Charge Waveform

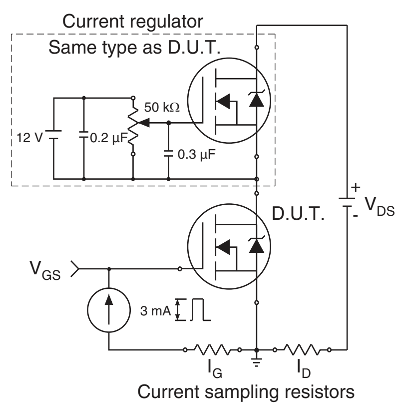
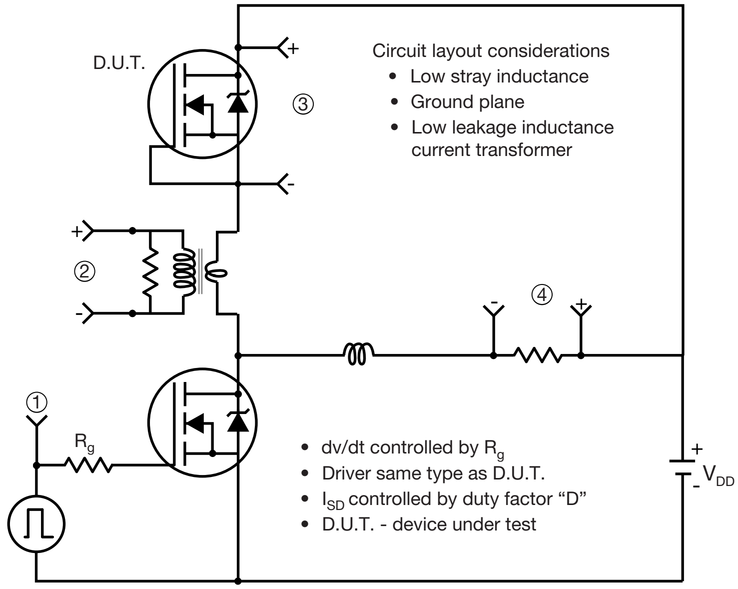
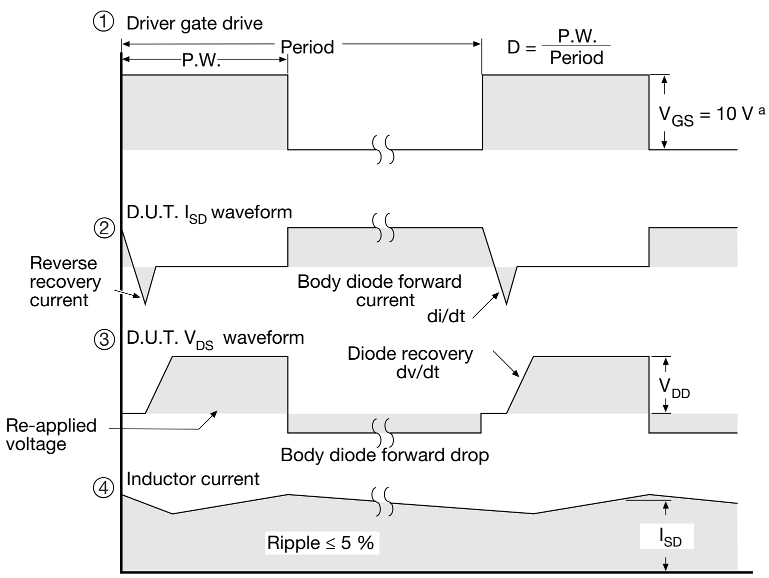


Fig. 13b - Gate Charge Test Circuit

For technical questions, contact: hvm@vishay.com

Peak Diode Recovery dv/dt Test Circuit





Note

a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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